

Claim 30, line 2 (Page 89, line 15), after "device," insert --according to claim 28,--.

A¹
Claim 31 (amended) A [process of producing] method of writing data into a nonvolatile semiconductor memory device according to claim 28, wherein the FN tunneling film comprises any one of a nitride film, an oxynitride film, an aluminium oxide film, a tantalum film and BST (BaSrTiO₃) film, having an FN tunneling electroconductivity.

Claim 33, line 1 (Page 90, line 5), change "dat" to --data--.

Claim 36, line 5 (Page 91, line 9), delete "a".

Claim 37, line 5 (Page 91, line 16), after "bias" delete "a"..

Claim 42, line 22 (Page 94, line 6), change "transistors" to --transistor--.

Claim 44, line 18 (Page 95, line 5) after "spaced" insert --from--.

Claim 48, line 8 (Page 96, line 22), after "isolated" insert --from--.

IN THE ABSTRACT:

Page 98, lines 1 and 2, delete "NONVOLATILE SEMICONDUCTOR MEMORY
DEVICE AND PROCESS OF PRODUCTION AND WRITE METHOD
THEREOF".

Page 98, lines 22 and 23, delete "it is possible to provide".

Page 98, line 23, after "electrode" insert --is provided--.

Page 98, line 24, after "and" insert --a--.